

Description

The SI9926CDY-T1-GE3 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

General Features

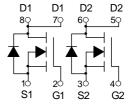
 $V_{DS} = 20V I_{D} = 8 A$

 $R_{DS(ON)} < 20m\Omega$ @ V_{GS} =4.5V

Application

Battery protection Load switch

Uninterruptible power supply



Dual N-Channel MOSFET

Package Marking and Ordering Information

| Product ID | Pack | Brand | Qty(PCS) |
|------------------|-------|------------|----------|
| SI9926CDY-T1-GE3 | SOP-8 | HXY MOSFET | 3000 |

Absolute Maximum Ratings (Tc=25℃unless otherwise noted)

| Symbol | Parameter | Limit | Unit |
|------------------|--|------------|------------|
| V _{DS} | Drain-Source Voltage | 20 | V |
| V _G S | Gate-Source Voltage | ±12 | V |
| I _D | Drain Current-Continuous | 8 | А |
| Ірм | Pulsed Drain Current | 28 | А |
| P _D | Maximum Power Dissipation | 2.25 | W |
| TJ,Tstg | Operating Junction and Storage Temperature Range | -55 To 150 | $^{\circ}$ |
| Rejc | Thermal Resistance,Junction-to-Case(Note 2) | 80 | °C/W |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Parameter | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|---|---------------------|---|------|------|------|------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | $V_{GS} = 0V, I_{D} = 250\mu A$ | 20 | - | - | V |
| Gate Leakage Current | lgss | V _{GS} = ±12V, V _{DS} = 0V | - | - | ±100 | nA |
| Drain Cut-off Current | IDSS | V _{DS} = 20V, V _{GS} = 0V | - | - | 1 | μA |
| Gate Threshold Voltage | V _{GS(th)} | V _{GS} = V _{DS} , I _D = 250μA | 0.45 | 0.7 | 1 | ٧ |
| Drain-Source On-State Resistance ³ | R _{DS(on)} | V _{GS} = 4.5V, I _D =5A | - | 13 | 20 | mΩ |
| | | V _{GS} = 2.5V, I _D = 4.7A | - | 18 | 30 | |
| | | V _{GS} = 1.8V, I _D = 4.3A | - | 28 | 57 | |
| Dynamic Characteristics⁴ | | | | | | |
| Input Capacitance | C _{iss} | V _{GS} = 0V, V _{DS} = 10V, f = 1MHz | - | 700 | - | pF |
| Output Capacitance | Coss | | - | 120 | - | |
| Reverse Transfer Capacitance | Crss | | - | 105 | - | |
| Switching Characteristics ⁴ | | | | | | |
| Total Gate Charge | Qg | V _{GS} = 4.5V, V _{DS} = 10V, I _D = 5A | - | 10.5 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 2 | - | |
| Gate-Drain Charge | \mathbf{Q}_{gd} | | - | 2.5 | - | |
| Turn-On Time | t _{d(on)} | V_{GS} = 5V, V_{DD} = 10V, I_{D} = 5A, R_{G} = 3 Ω , | - | 10 | - | ns |
| Rise Time | tr | | - | 20 | - | |
| Turn-Off Time | t _{d(off)} | | - | 32 | - | |
| Fall Time | t f | | - | 12 | - | |
| Source-Drain Diode Characteristics | | | | | | |
| Body Diode Voltage ³ | V _{SD} | I _S =4A, V _{GS} = 0V | - | - | 1.2 | V |
| Continuous Source Current | Is | | - | _ | 8 | А |

Notes:

- 1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C.
- 2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
- 3. Pulse Test: Pulse width≤300µs, duty cycle≤2%.
- 4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

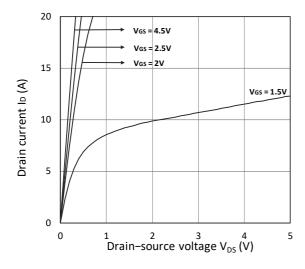


Figure 1. Output Characteristics

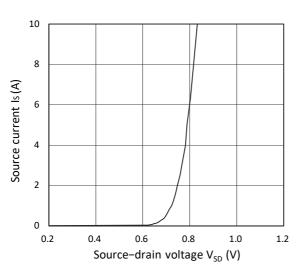


Figure 3. Forward Characteristics of Reverse

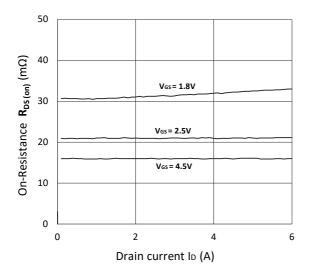


Figure 5. $R_{DS(ON)}$ vs. I_D

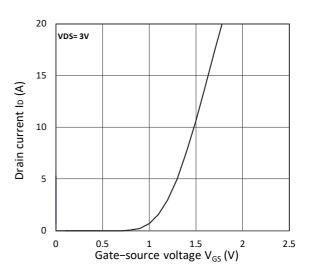


Figure 2. Transfer Characteristics

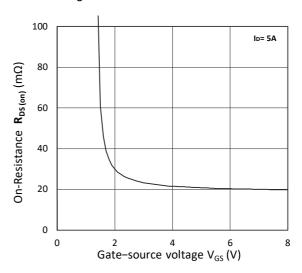


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

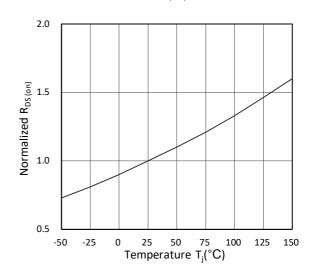


Figure 6. Normalized $R_{\text{DS(on)}}$ vs. Temperature

10000

1000

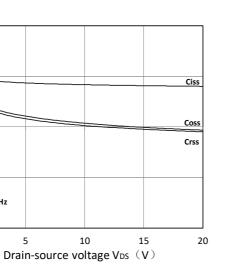
100

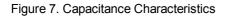
10

1

F=1.0MHz

Capacitance (pF)





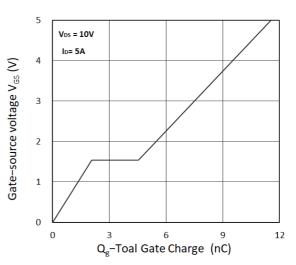
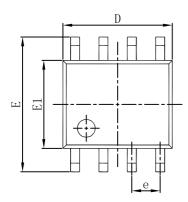
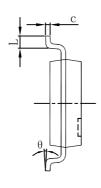
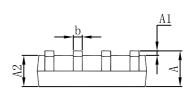


Figure 8. Gate Charge Characteristics

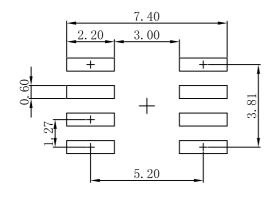
SOP-8 Package Outline Dimensions







| Symbol | Dimensions In Millimeters | | Dimensions In Inches | | | |
|--------|---------------------------|-------------|----------------------|-------------|--|--|
| | Min | Max | Min | Max | | |
| A | 1. 350 | 1.750 | 0.053 | 0.069 | | |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 | | |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 | | |
| b | 0.330 | 0.510 | 0.013 | 0.020 | | |
| c | 0.170 | 0.250 | 0.007 | 0.010 | | |
| D | 4.800 | 5.000 | 0.189 | 0.197 | | |
| e | 1. 270 (| 1.270 (BSC) | | 0.050 (BSC) | | |
| E | 5.800 | 6.200 | 0. 228 | 0. 244 | | |
| E1 | 3.800 | 4.000 | 0.150 | 0. 157 | | |
| L | 0.400 | 1.270 | 0.016 | 0.050 | | |
| θ | 0° | 8° | 0° | 8° | | |



- Note:
 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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